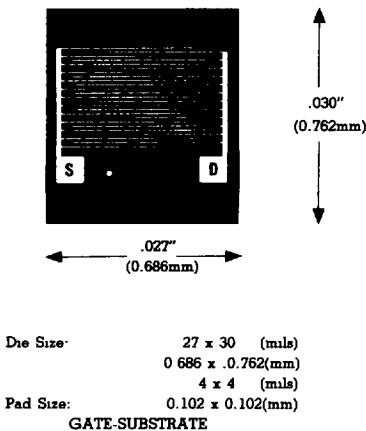


PRODUCT CATALOG

N-CHANNEL JUNCTION FET

CHIP NUMBER

FN9



CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

- It is advisable that:
- a) the die be eutectically mounted with gold silicon preform 98/2%.
 - b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-25	-30	-45	V	$V_{DS} = 0, I_G = 1\mu A$
IDSS	100	400	700	mA	$V_{DS} = 5V, V_{GS} = 0$ (pulse test)
gfs		10		mmho	$V_{DG} = 10V, I_D = 2mA$
IGSS		-50	-500	pA	$V_{GS} = -15V, V_{DS} = 0$
rDS	4.5	6.0	20	Ω	$V_{DS} = 100mV, V_{GS} = 0$
VGS(off)	-0.5	5.0	12.0	V	$V_{DS} = 5V, I_D = 3nA$
Crss		12	20	pF	$V_{DG} = 10V, V_{DG} = 0, f = 1MHz$
Ciss		25	35	pF	$V_{SG} = 10V, V_{DS} = 0, f = 1MHz$
en		5.0		nV/√Hz	$V_{DG} = 15V, I_D = 2mA, f = 10Hz$

TYPICAL DEVICE TYPES: 2N5432 - 2N5434, SDF1000 series

CHIP TYPE FN9

